

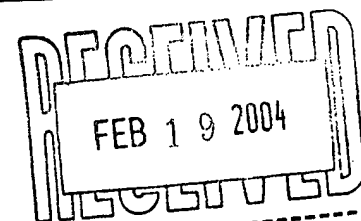
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Sadaka et al.
Serial No.: 10/029,903
Filing Date: 12/21/01
Examiner: Pham Long
Art Unit: 2814
Title: A CHEMISTRY FOR ETCHING QUATERNARY INTERFACE
LAYERS ON InGaAsP MOSTLY FORMED BETWEEN GaAs
AND In_xGa_(1-x)P LAYERS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

CERTIFICATION OF FACSIMILE TRANSMISSION	
I hereby certify that this paper is being transmitted via facsimile to the Patent and Trademark Office on the date shown below.	
January 3, 2004	
Date	Signature
Printed Name	John A. Fortkort

RESPONSE TO OFFICE ACTION



Dear Sir:

In response to the Office Action dated October 3, 2003,
Applicant hereby responds as follows.

Amendments to the Specification: No amendments to the specification are included with this response.

Amendments to the Claims are reflected in the listing of claims which begins on Page 3 of this paper.

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JAN 05 2004

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Amendments to the Drawings: No amendments to the drawings are included with this response.

Remarks/Arguments begin on page 10 of this paper.